

ABSTRACT OF THE DISCLOSURE

SILICATE GATE DIELECTRIC

413,462

- 5 A method of forming a silicate dielectric having superior electrical properties comprising forming a metal oxide layer on a Si-containing semiconductor material and reacting the metal oxide with the underlying Si-containing material in the presence of an oxidizing gas
- 10 is provided. Semiconductor structures comprising the metal silicate formed over a SiO_2 layer are also disclosed herein.

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